



Linde Electronics List of Gases

	CLEANING	DEPO- SITION	DOPING	ETCH	ANNEALING	LITHO- GRAPHY	PURGING
Ar (Argon)							●
Ar/F ₂ /Ne (Argon/Fluorine/Neon - ArF laser)						●	
Ar/Xe/Ne (Argon/Xenon/Neon - ArF laser)						●	
AsH ₃ (Arsine)		●	●				
BF ₃ (Boron trifluoride)			●				
¹¹ BF ₃ (Boron-11 trifluoride)			●				
¹¹ B ₂ H ₆ (Enriched diborane)			●				
B ₂ H ₆ (Diborane)			●				
BCl ₃ (Boron trichloride)				●			
C ₂ F ₆ (Hexafluoroethane) Halocarbon 116	●	●		●			
C ₂ H ₂ (Acetylene)		●					
C ₃ F ₈ (Octafluoropropane) Halocarbon 218				●			
C ₃ H ₆ (Propylene)		●					
C ₄ F ₆ (Hexafluoro-3- butadiene) Halocarbon 2316				●			
C ₄ F ₈ (Octofluorocyclo butane) Halocarbon 318				●			
C ₅ F ₈ (Octofluorocyclo pentene) Halocarbon c1418				●			
CF ₄ (Carbon tetrafluoride) Halocarbon 14	●			●			

	CLEANING	DEPO- SITION	DOPING	ETCH	ANNEALING	LITHO- GRAPHY	PURGING
CH ₂ F ₂ (Difluoromethane) Halocarbon 32				●			
C ₂ HF ₅ (Pentafluoroethane) CH ₃ F (Fluoromethane) Halocarbon 41				●			
CH ₄ (Methane) CHF ₃ (Trifluoromethane) Halocarbon 23		●		●			
Cl ₂ (Chlorine)	●			●			
ClF ₃ (Chlorine trifluoride)	●						
CO (Carbon monoxide)		●		●			
CO ₂ (Carbon dioxide)				●		●	
COS (Carbonyl sulfide)		●					
D ₂ (Deuterium)					●		
DEZ (Diethylzinc)		●	●				
F ₂ (Fluorine)	●						
F ₂ /N ₂ (Fluorine/Nitrogen)	●						
GeCl ₄ (Germanium tetrachloride)		●					
GeH ₄ (Germane)		●	●				
He (Helium)							●
H ₂ (Hydrogen)					●	●	●
H ₂ S (Hydrogen sulfide)		●					

	CLEANING	DEPO- SITION	DOPING	ETCH	ANNEALING	LITHO- GRAPHY	PURGING
H ₂ Se (Hydrogen selenide)	●						
HBr (Hydrogen bromide)				●			
HCDS (Hexachlorodisilane)		●					
HCl (Hydrogen chloride)		●		●			
HF (Hydrogen fluoride)				●			
Kr (Krypton)				●		●	
Kr/F ₂ /Ne (Krypton/Fluorine/Neon - KrF laser)						●	
Kr/Ne (Krypton/Neon - KrF laser)						●	
N ₂ (Nitrogen)							●
N ₂ O (Nitrous oxide)		●		●			
ND ₃ (Deuterated ammonia)		●					
Ne (Neon)						●	
Ne/HCl/H ₂ mixture (Neon/Hydrogen chloride/Hydrogen)						●	
NF ₃ (Nitrogen trifluoride)	●			●			
NH ₃ (Ammonia)		●					
NO (Nitric oxide)		●		●			
O ₂ (Oxygen)	●	●		●			
PH ₃ (Phosphine)		●	●				

	CLEANING	DEPO- SITION	DOPING	ETCH	ANNEALING	LITHO- GRAPHY	PURGING
SF ₆ (Sulfur hexafluoride)	●			●			
Si ₂ Cl ₆ (HCDS - Hexachlorodisilane)		●					
Si ₂ H ₆ (Disilane)		●					
SiCl ₄ (Tetrachlorosilane - silicon tetrachloride)		●					
SiD ₄ (Deuterated silane)		●					
SiF ₄ (Tetrafluorosilane - also know as silicon tetrafluoride)		●		●			
SiH ₂ Cl ₂ (Dichlorosilane)		●					
SiH ₄ (Silane)		●					
SiHCl ₃ (TCS - Trichlorosilane)		●					
SO ₂ (Sulfur dioxide)		●					
TEA (Triethylaluminum)		●					
TMA (Trimethylaluminum)		●					
TMB (Trimethylboron)			●				
TMS (3MS - Trimethylsilane)		●					
WF ₆ (Tungsten hexafluoride)		●					
Xe (Xenon)				●		●	
XeF ₂ (Xenon difluoride)				●			
Mixtures (calibration, etc.)							

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